

# SILICON POWER TRANSISTOR 2SC3570

# NPN SILICON TRIPLE DIFFUSED TRANSISTOR FOR HIGH-VOLTAGE HIGH-SPEED SWITCHING

The 2SC3570 is a mold power transistor developed for high-voltage high-speed switching, and is ideal for use in drivers such as switching regulators, DC/DC converters, and high-frequency power amplifiers.

#### **FEATURES**

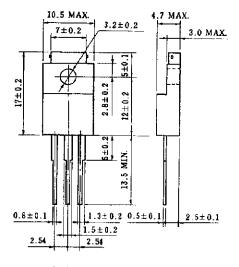
- Mold package that does not require an insulating board or insulation bushing
- Low collector saturation voltage:
   Vce(sat) = 1.0 V MAX. (@ 2 A)
- Fast switching speed:
   tf ≤ 0.7 µs MAX. (@ 2 A)
- Wide base reverse-bias SOA:
   Vcex(SUS) = 450 V MIN. (@ 2 A)

#### ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

| Parameter                    | Symbol                     | Ratings     | Unit |
|------------------------------|----------------------------|-------------|------|
| Collector to base voltage    | Vcво                       | 500         | V    |
| Collector to emitter voltage | VCEO                       | 400         | V    |
| Emitter to base voltage      | V <sub>EBO</sub>           | 8.0         | V    |
| Collector current (DC)       | Ic(DC)                     | 5.0         | Α    |
| Collector current (pulse)    | Ic(pulse)*                 | 10          | Α    |
| Base current (DC)            | I <sub>B(DC)</sub>         | 2.5         | Α    |
| Total power dissipation      | P <sub>T</sub> (Tc = 25°C) | 25          | W    |
| Total power dissipation      | P⊤ (Ta = 25°C)             | 2.0         | W    |
| Junction temperature         | Tj                         | 150         | °C   |
| Storage temperature          | Tstg                       | -55 to +150 | °C   |

<sup>\*</sup> PW  $\leq$  300  $\mu$ s, duty cycle  $\leq$  10%

#### PACKAGE DRAWING (UNIT: mm)





Electrode Connection

- 1. Base
- 2. Collector
- 3 Emitter

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## **ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

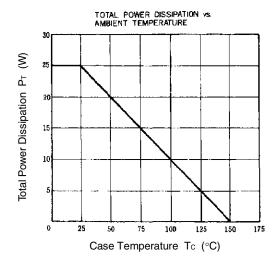
| Parameter                    | Symbol                 | Conditions  | MIN. | TYP. | MAX. | Unit |
|------------------------------|------------------------|---|------|------|------|------|
| Collector to emitter voltage | VCEO(SUS)              | Ic = 2.0 A, I <sub>B1</sub> = 0.4 A, L = 1 mH   | 400  |      |      | ٧    |
| Collector to emitter voltage | VCEX(SUS)1             | Ic = 2.0 A, IB1 = $-$ IB2 = 0.4 A, L = 180 $\mu$ H, clamped                                       | 450  |      |      | V    |
| Collector to emitter voltage | VCEX(SUS)2             | Ic = 4.0 A, I <sub>B1</sub> = 0.8 A, $-I_{B2}$ = 0.4 A, 400<br>L = 180 $\mu$ H, clamped           |      |      |      | V    |
| Collector cutoff current     | Ісво                   | V <sub>CB</sub> = 400 V, I <sub>E</sub> = 0   |      |      | 10   | μΑ   |
| Collector cutoff current     | ICER                   | $V_{CE}=400~V,~R_{BE}=51~\Omega,~Ta=125^{\circ}C$   |      |      | 1.0  | mA   |
| Collector cutoff current     | ICEX1                  | $V_{CE} = 400 \text{ V}, V_{BE(OFF)} = -1.5 \text{ V}$  |      |      | 10   | μΑ   |
| Collector cutoff current     | ICEX2                  | $V_{CE} = 400 \text{ V}, V_{BE(OFF)} = -1.5 \text{ V},$ $Ta = 125^{\circ}C$                       |      |      | 1.0  | mA   |
| Emitter cutoff current       | ІЕВО                   | V <sub>EB</sub> = 5.0 V, I <sub>C</sub> = 0   |      |      | 10   | μΑ   |
| DC current gain              | hFE1*                  | VcE = 5.0 V, Ic = 0.5 A   | 20   |      | 80   |      |
| DC current gain              | hFE2*                  | VcE = 5.0 V, Ic = 2.0 A   | 10   |      |      |      |
| Collector saturation voltage | V <sub>CE(sat)</sub> * | Ic = 2.0 A, I <sub>B</sub> = 0.4 A  |      |      | 1.0  | ٧    |
| Base saturation voltage      | V <sub>BE(sat)</sub> * | Ic = 2.0 A, I <sub>B</sub> = 0.4 A  |      |      | 1.2  | V    |
| Turn-on time                 | ton                    | $Ic = 2.0 \text{ A}, R_L = 75 \Omega,$  |      |      | 1.0  | μs   |
| Storage time                 | tstg                   | $I_{B1} = -I_{B2} = 0.4 \text{ A}, \text{ V}_{CC} \cong 150 \text{ V}$ Refer to the test circuit. |      |      | 2.0  | μs   |
| Fall time                    | tf                     | Tieler to the test circuit.   |      |      | 0.7  | μs   |

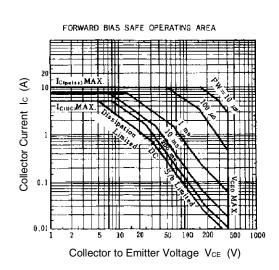
<sup>\*</sup> Pulse test PW  $\leq$  350  $\mu$ s, duty cycle  $\leq$  2%

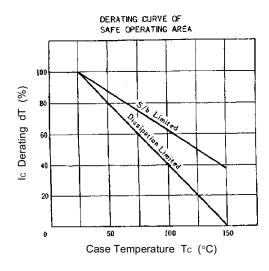
#### **hfe CLASSIFICATION**

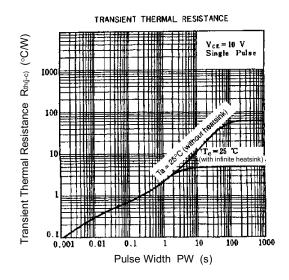
| Marking          | M        | L        | К        |
|------------------|----------|----------|----------|
| h <sub>FE1</sub> | 20 to 40 | 30 to 60 | 40 to 80 |

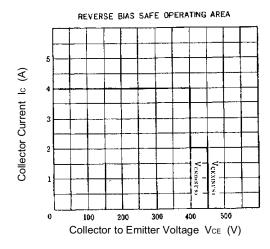
# TYPICAL CHARACTERISTICS (Ta = 25°C)

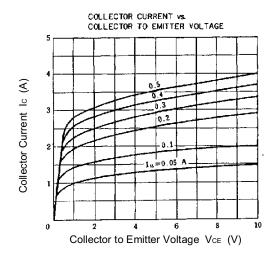


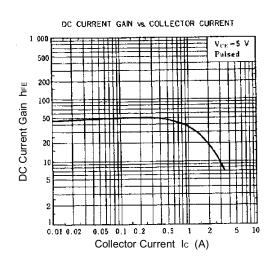


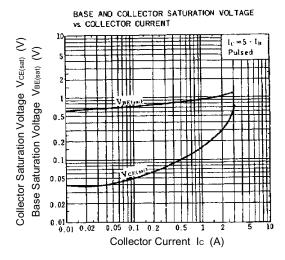




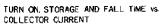


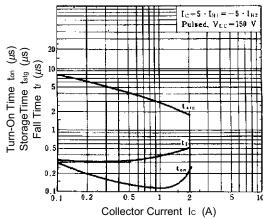




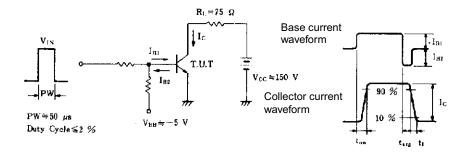


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## SWITCHING TIME ( $t_{\text{onr}}$ $t_{\text{stg}},$ $t_{\text{f}})$ TEST CIRCUIT





[MEMO]

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